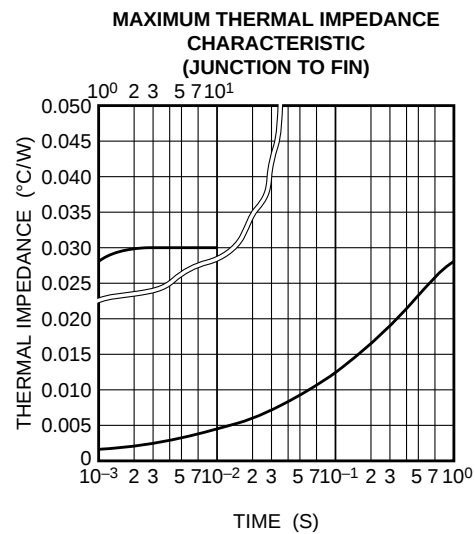
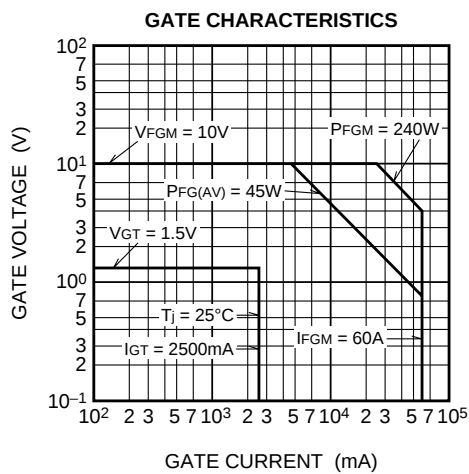
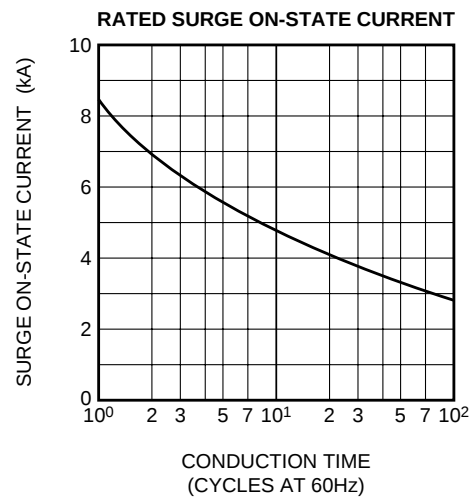
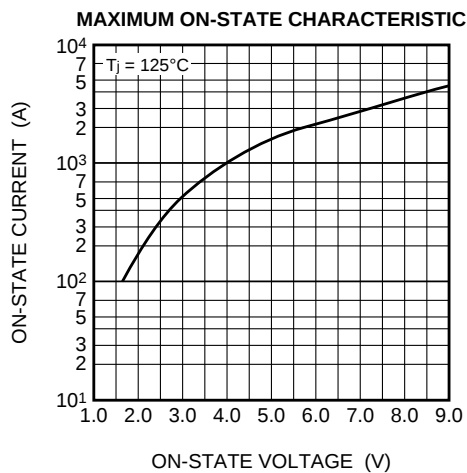


FG1000BV-90DAHIGH POWER INVERTER USE
PRESS PACK TYPE**ELECTRICAL CHARACTERISTICS**

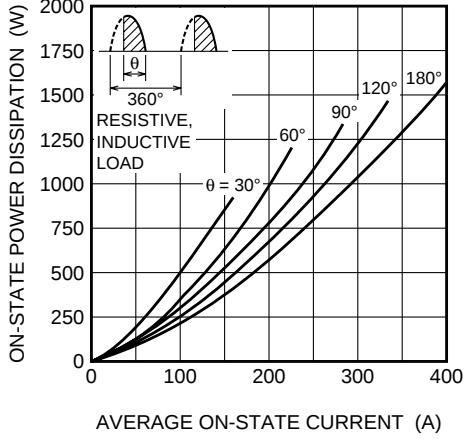
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{TM}	On-state voltage	T _J = 125°C, I _{TM} = 1000A, Instantaneous measurment	—	—	4.0	V
I _{RRM}	Repetitive peak reverse current	T _J = 125°C, V _{RRM} Applied	—	—	100	mA
I _{DRM}	Repetitive peak off-state current	T _J = 125°C, V _{DRM} Applied, V _{GK} = -2V	—	—	100	mA
I _{RG}	Reverse gate current	T _J = 125°C, V _{RG} = 17V	—	—	100	mA
dv/dt	Critical rate of rise of off-state voltage	T _J = 125°C, V _D = 2250V, V _{GK} = -2V	1000	—	—	V/μs
t _{gt}	Turn-on time	T _J = 125°C, I _{TM} = 1000A, I _{GM} = 20A, V _D = 2250V	—	—	10	μs
t _{gq}	Turn-off time	T _J = 125°C, I _{TM} = 1000A, V _{DM} = 3375V, diGQ/dt = -30A/μs V _{RG} = 17V, C _S = 0.7μF, L _S = 0.3μH	—	—	20	μs
I _{GQM}	Peak gate turn-off current		—	330	—	A
V _{GT}	Gate trigger voltage	DC METHOD : V _D = 24V, R _L = 0.1Ω, T _J = 25°C	—	—	1.5	V
I _{GT}	Gate trigger current		—	—	2500	mA
R _{th(j-f)}	Thermal resistance	Junction to fin	—	—	0.03	°C/W

PERFORMANCE CURVES

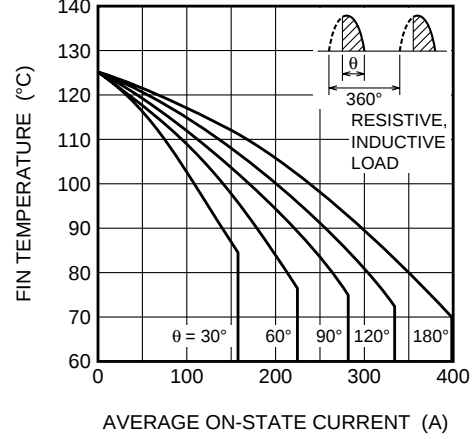
FG1000BV-90DA

HIGH POWER INVERTER USE
PRESS PACK TYPE

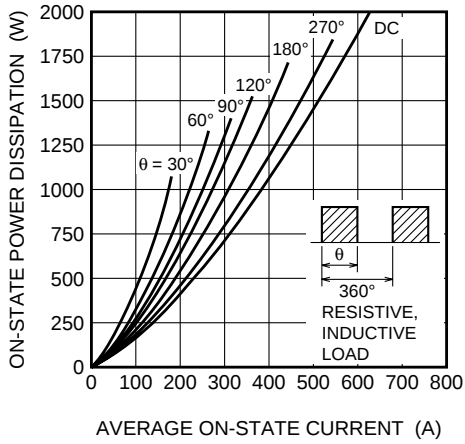
MAXIMUM ON-STATE POWER DISSIPATION
CHARACTERISTICS
(SINGLE-PHASE HALF WAVE)



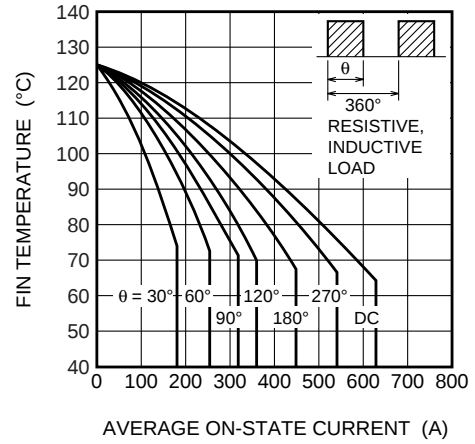
ALLOWABLE FIN TEMPERATURE VS.
AVERAGE ON-STATE CURRENT
(SINGLE-PHASE HALF WAVE)



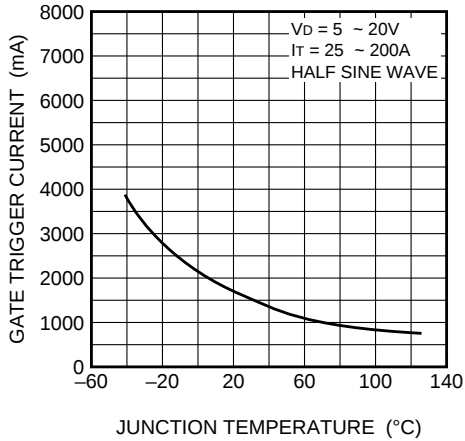
MAXIMUM ON-STATE POWER DISSIPATION
CHARACTERISTICS
(RECTANGULAR WAVE)



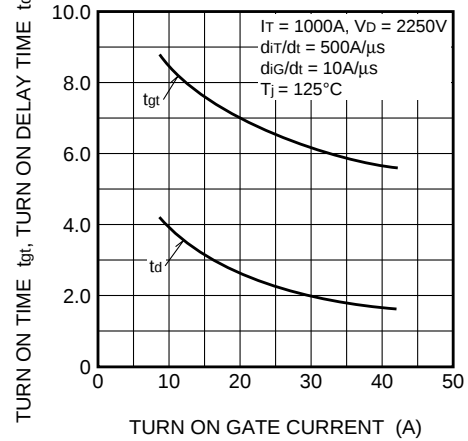
ALLOWABLE FIN TEMPERATURE VS.
AVERAGE ON-STATE CURRENT
(RECTANGULAR WAVE)



GATE TRIGGER CURRENT VS.
JUNCTION TEMPERATURE
(TYPICAL)



TURN ON TIME, TURN ON DELAY TIME
VS. TURN ON GATE CURRENT
(TYPICAL)



FG1000BV-90DA

HIGH POWER INVERTER USE
PRESS PACK TYPE

